



# 415  
118103  
Mollish

Atty. Docket No. 8029-1041

RECEIVED  
PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE  
JAN 3 2003  
TECHNOLOGY CENTER 2800

In re application of

Masaru TSUKIJI

Confirmation No. 4695

Serial No. 09/761,693

GROUP 2826

Filed January 18, 2001

Examiner Fetsum Abraham

STRUCTURE AND MANUFACTURING  
METHOD OF NON-VOLATILE FLASH  
MEMORY

AMENDMENT

Commissioner for Patents

Washington, D.C. 20231

Sir:

Responsive to the Official Action of October 21, 2002,  
please amend the above-identified application as follows:

IN THE CLAIMS:

Amend claim 3 as follows:

--3. (amended) A structure of a non-volatile flash memory that is a NOR type non-volatile flash memory, provides floating gates and a common source line, wherein:

an impurity gradient distribution of a source in a memory cell adjacent to where said source joins a semiconductor substrate is gradual.--

REMARKS

The indication that claims 1-2 and 4-12 have been allowed is acknowledged with thanks. Claim 3 was rejected under